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PN - JP2001332653 A 20011130
TI - (A) SEMICONDUCTOR DEVICE
AB - (A) PROBLEM TO BE SOLVED: To provide a semiconductor device, which is constituted in a high-density external wiring structure and also prevents external connection wirings from being disconnected by relaxing a stress which is generated in a semiconductor substrate after the substrate is mounted on a substrate. SOLUTION: A semiconductor device is constituted in a structure that a plurality of external connection electrodes 8 are provided on a semiconductor substrate 1 and rewiring patterns 6 for connecting electrodes 2 on the substrate 1 with the electrodes 8 are respectively wired in the direction, in which the effect of a strain exerted on the patterns 6 after the substrate 1 is mounted on an executing substrate is weak, in the vicinities of the electrodes 8. That is, a wiring is designed so that as the electrodes 8 are apt to exert a strain due to a thermal stress in the directions to link the center 11 of the substrate 1 with the electrodes 8, the patterns 6 are never led out in these directions. Consequently, the strain which is generated in the patterns 6 after the substrate 1 is mounted on the substrate is reduced. Moreover, an adverse effect due to a strain stress can be prevented without widening the width of the external connection wirings 8. As the result, the semiconductor device can be constituted into a semiconductor device of a high-density wiring structure.

FI - H01L21/60&311S; H01L21/88&T; H01L21/92&602N; H01L23/12&L; H01L23/12&Q; H01L23/12&501P
PA - (A) SHARP KK
IN - (A) TANAKA KAZUMI; SUMIKAWA MASAHIITO
AP - JP20000154788 20000525
PR - JP20000154788 20000525
DT - I

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